

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ Max	I_D Max @ $T_A = +25^\circ\text{C}$
-30V	2.4Ω @ $V_{GS} = -10\text{V}$	-400mA
	4Ω @ $V_{GS} = -4.5\text{V}$	-300mA
	16Ω @ $V_{GS} = -2.5\text{V}$	-50mA

Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load Switch
- Portable Applications
- Power Management Functions

Features

- Low On-Resistance
- Ultra-Small Surfaced Mount Package
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

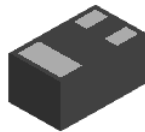
Mechanical Data

- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208 (4)
- Weight: 0.001 grams (approximate)

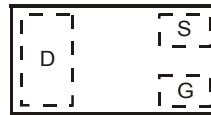


ESD PROTECTED

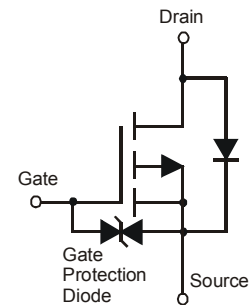
X1-DFN1006-3



Bottom View



Top View



Equivalent Circuit

Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Quantity per reel
DMP32D4SFB-7B	XP	7	10,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



XP = Product Type Marking Code

 Top View
 Bar Denotes Gate and Source Side

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Drain Current (Note 5)	$V_{GS} = -10\text{V}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	-400 -300	mA
Continuous Drain Current (Note 6)	$V_{GS} = -10\text{V}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	-500 -400	mA
Pulsed Drain Current (Note 5)			I_{DM}	-1	A
Maximum Body Diode continuous Current			I_S	-800	mA

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation	(Note 5)	0.5	W
	(Note 6)	1.2	
Thermal Resistance, Junction to Ambient	(Note 5)	273	$^\circ\text{C}/\text{W}$
	(Note 6)	105	
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	-	-	V	$V_{GS} = 0\text{V}, I_D = -1\text{mA}$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	I_{DSS}	-	-	-1	μA	$V_{DS} = -30\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	-	-	± 10	μA	$V_{GS} = \pm 16\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	-1.3	-	-2.3	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	-	-	2.4	Ω	$V_{GS} = -10\text{V}, I_D = -200\text{mA}$
				4		$V_{GS} = -4.5\text{V}, I_D = -200\text{mA}$
				16		$V_{GS} = -2.5\text{V}, I_D = -10\text{mA}$
Forward Transfer Admittance	$ Y_{fs} $	-	6	-	S	$V_{DS} = -10\text{V}, I_D = -400\text{mA}$
Diode Forward Voltage	V_{SD}	-	0.8	1.2	V	$V_{GS} = 0\text{V}, I_S = -300\text{mA}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	-	51	-	pF	$V_{DS} = -15\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	-	11	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	9	-	pF	
Total Gate Charge	Q_g	-	0.6	-	nC	$V_{GS} = -4.5\text{V}$
Total Gate Charge	Q_g	-	1.3	-	nC	
Gate-Source Charge	Q_{gs}	-	0.2	-	nC	$V_{GS} = -10\text{V}$
Gate-Drain Charge	Q_{gd}	-	0.2	-	nC	
Turn-On Delay Time	$t_{D(on)}$	-	3.6	-	ns	$V_{DS} = -10\text{V}, I_D = -200\text{mA}$
Turn-On Rise Time	t_r	-	8.5	-	ns	
Turn-Off Delay Time	$t_{D(off)}$	-	31.3	-	ns	
Turn-Off Fall Time	t_f	-	20.2	-	ns	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

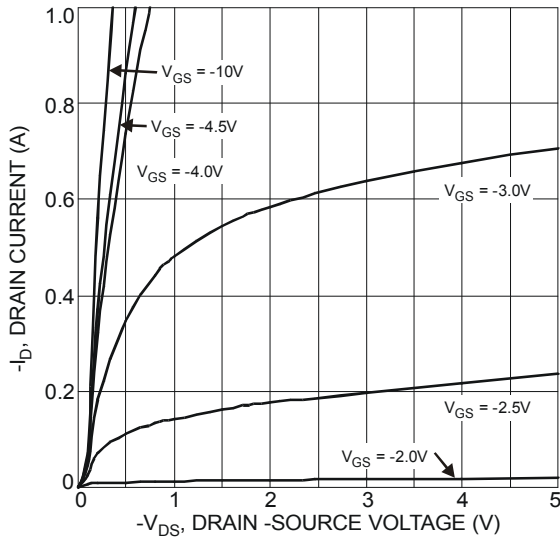


Figure 1 Typical Output Characteristics

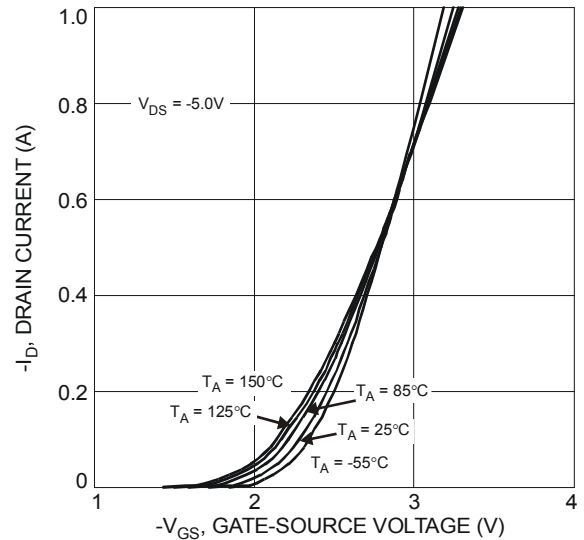


Figure 2 Typical Transfer Characteristics

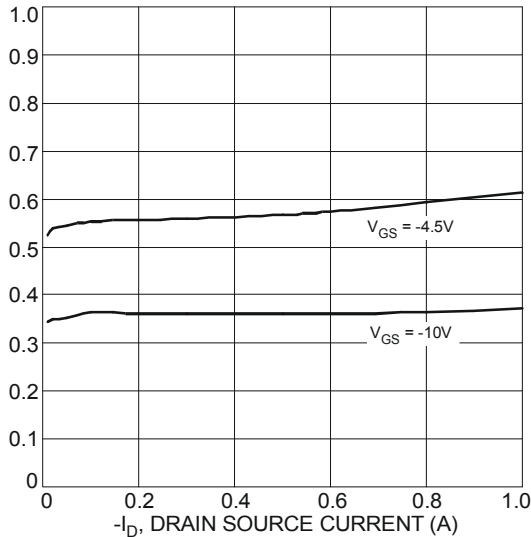


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

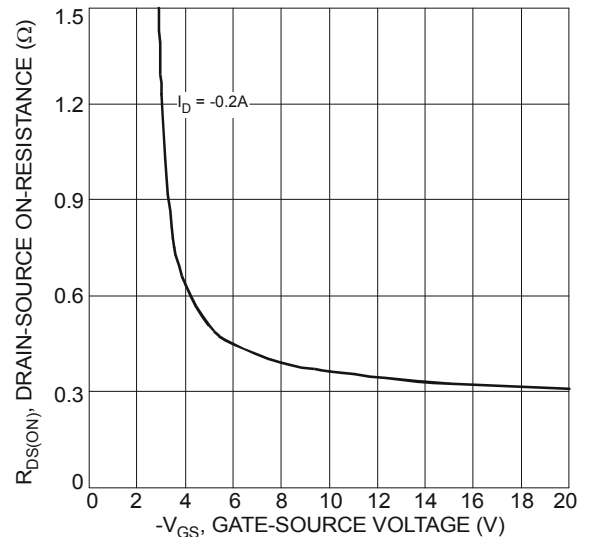


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

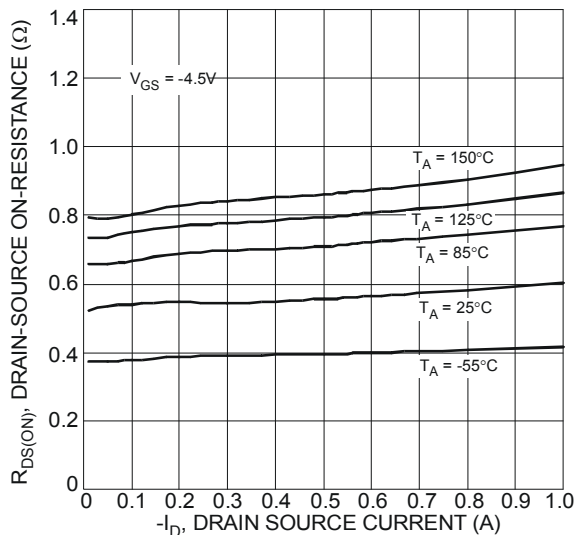


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

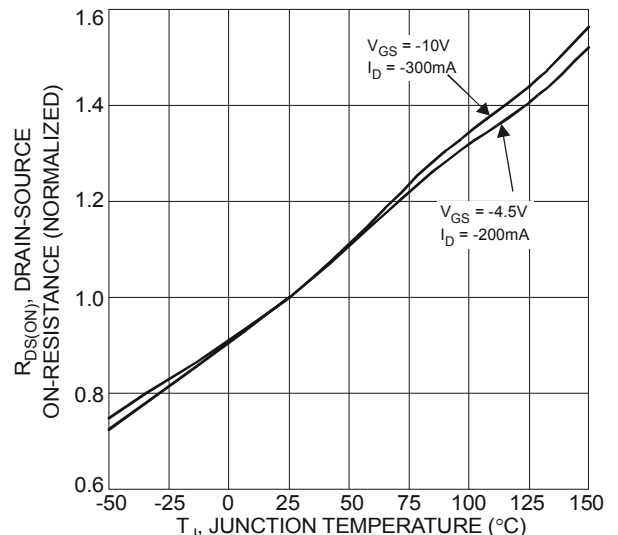


Figure 6 On-Resistance Variation with Temperature

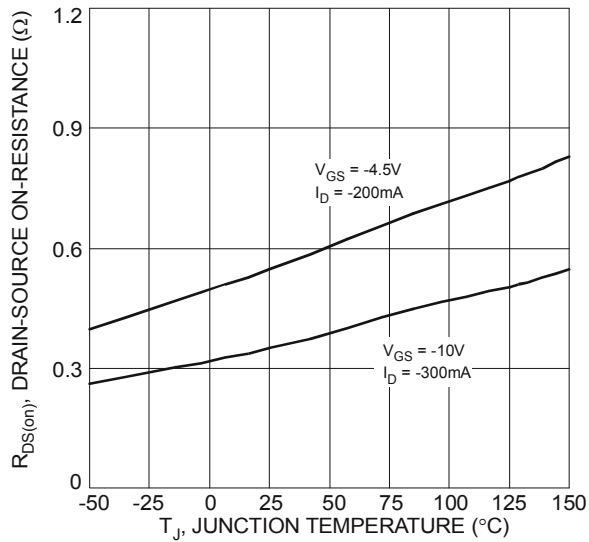


Figure 7 On-Resistance Variation with Temperature

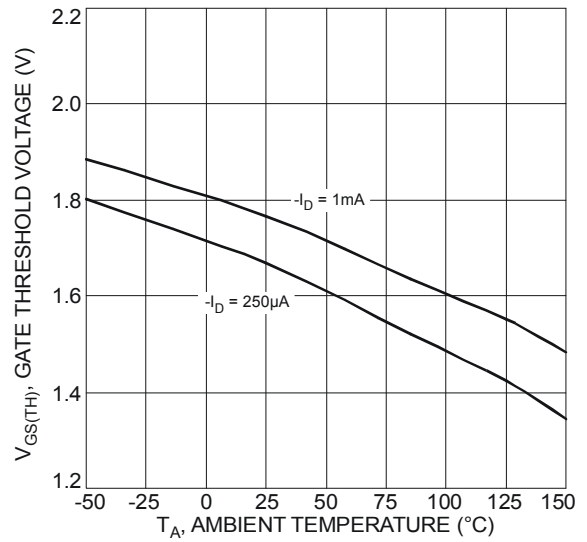


Figure 8 Gate Threshold Variation vs. Ambient Temperature

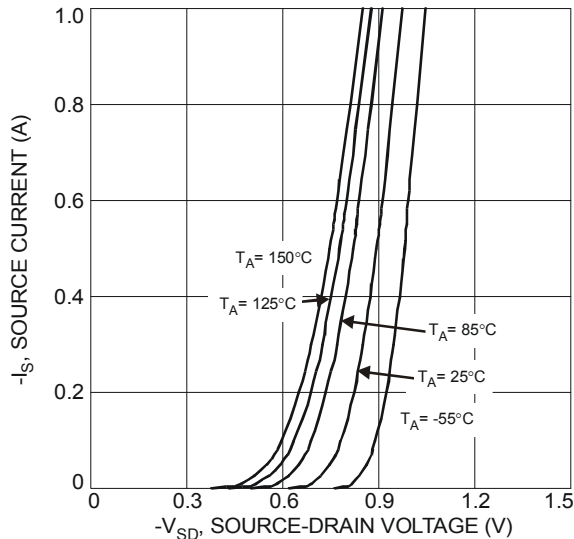


Figure 9 Diode Forward Voltage vs. Current

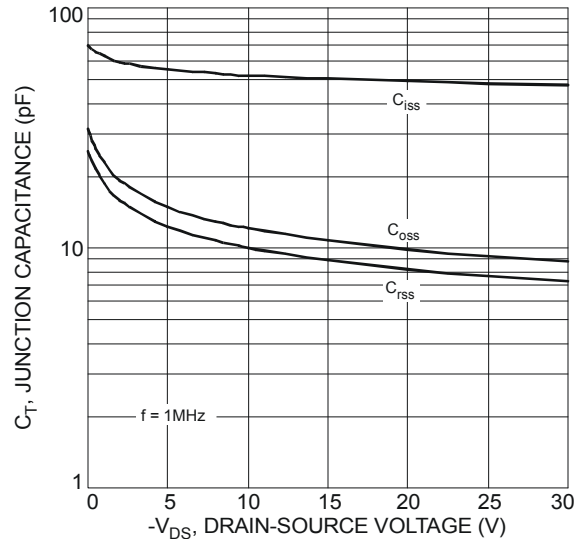


Figure 10 Typical Junction Capacitance

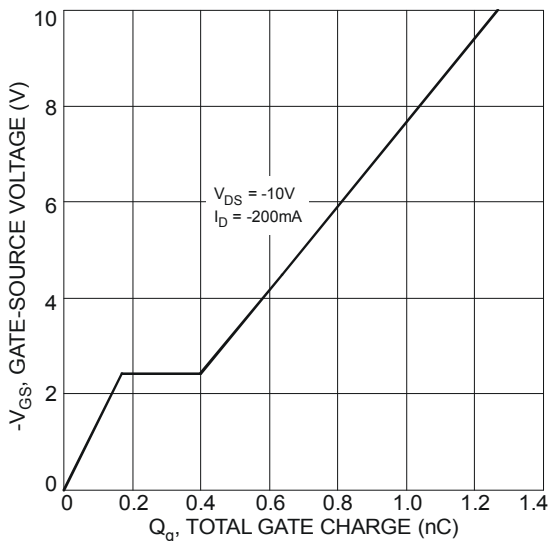
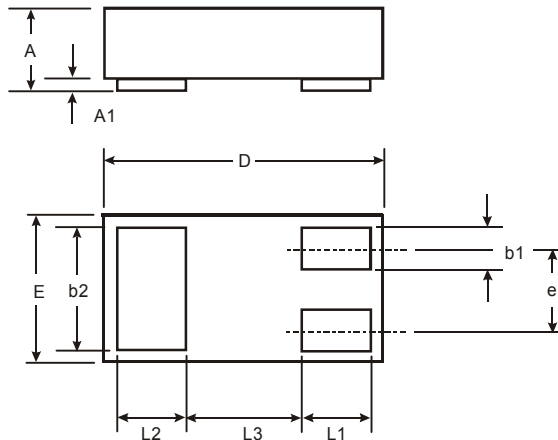


Figure 11 Gate-Charge Characteristics

Package Outline Dimensions

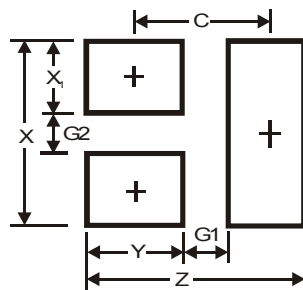
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



X1-DFN1006-3			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0	0.05	0.03
b1	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	—	—	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	—	—	0.40
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	1.1
G1	0.3
G2	0.2
X	0.7
X1	0.25
Y	0.4
C	0.7

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